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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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HSS83

Silicon Epitaxial Planar Diode for High Voltage Switching

RENESAS

ADE-208-177B (Z)

Rev.2 Oct. 2000

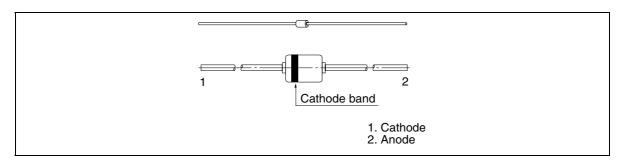
Features

- High reverse voltage. ($V_R = 250 \text{ V}$)
- Suitable for 5 mm pitch high speed automatically insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Туре No.	Cathode band	Package Code
HSS83	Black	MHD

Pin Arrangement



HSS83

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit
Peak reverse voltage	V _{RM} * ¹	300	V
Reverse voltage	V _R	250	V
Peak forward current	I _{FM}	625	mA
Non-Repetitive peak forward surge current	I _{FSM} ∗ ²	1	А
Average forward current	I _o	150	mA
Power dissipation	Pd	400	mW
Junction temperature	Tj	200	٥°
Storage temperature	Tstg	-65 to +175	°C

Notes: 1. Reverse voltage in excess of peak reverse voltage may deteriorate electrical characteristic.

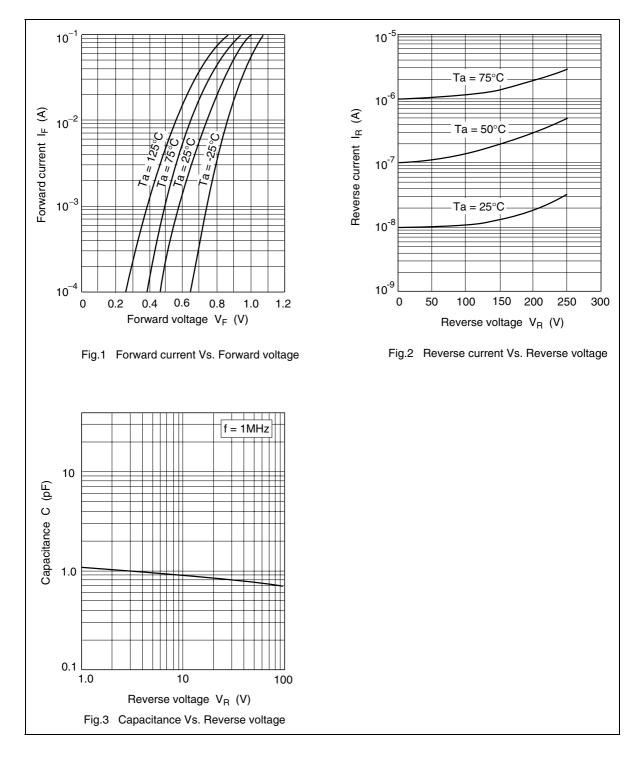
2. Within 1s forward surge current.

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V _F		_	1.0	V	I _F = 100 mA
Reverse current	I _{R1}			0.2	μΑ	V _R = 250 V
	I _{R2}		_	100		V _R = 300 V
Capacitance	С		1.5		рF	$V_{_{\mathrm{H}}} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$
Reverse recovery time	t _{rr}			100	ns	$I_{_{\rm F}} = I_{_{\rm R}} = 30$ mA, Irr = 3mA, $R_{_{\rm L}} = 100 \ \Omega$

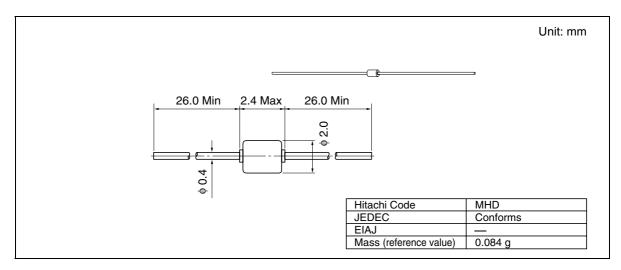
Main Characteristic



RENESAS

HSS83

Package Dimensions





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